

Paul Harrison

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3,621
ext. citations

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L-index

#	Paper	IF	Citations
167	2005,		417
166	Band structure calculations of SiGeSn alloys: achieving direct band gap materials. <i>Semiconductor Science and Technology</i> , 2007 , 22, 742-748	1.8	165
165	Band engineering and growth of tensile strained Ge/(Si)GeSn heterostructures for tunnel field effect transistors. <i>Applied Physics Letters</i> , 2013 , 102, 192103	3.4	112
164	Terahertz imaging through self-mixing in a quantum cascade laser. <i>Optics Letters</i> , 2011 , 36, 2587-9	3	108
163	Self-consistent scattering theory of transport and output characteristics of quantum cascade lasers. <i>Journal of Applied Physics</i> , 2002 , 91, 9019-9026	2.5	100
162	Simulation and design of GaN/AlGaIn far-infrared (834 μ m) quantum-cascade laser. <i>Applied Physics Letters</i> , 2004 , 84, 2995-2997	3.4	72
161	Swept-frequency feedback interferometry using terahertz frequency QCLs: a method for imaging and materials analysis. <i>Optics Express</i> , 2013 , 21, 22194-205	3.3	62
160	The nature of the electron distribution functions in quantum cascade lasers. <i>Applied Physics Letters</i> , 1999 , 75, 2800-2802	3.4	62
159	Interwell intersubband electroluminescence from Si/SiGe quantum cascade emitters. <i>Applied Physics Letters</i> , 2003 , 83, 4092-4094	3.4	60
158	Mechanisms of temperature performance degradation in terahertz quantum-cascade lasers. <i>Applied Physics Letters</i> , 2003 , 82, 1347-1349	3.4	59
157	Self-consistent solutions to the intersubband rate equations in quantum cascade lasers: Analysis of a GaAs/Al _x Ga _{1-x} As device. <i>Journal of Applied Physics</i> , 2001 , 89, 3084-3090	2.5	57
156	Mechanisms of dynamic range limitations in GaAs/AlGaAs quantum-cascade lasers: Influence of injector doping. <i>Applied Physics Letters</i> , 2005 , 86, 2111-17	3.4	55
155	Finite difference method for solving the Schrödinger equation with band nonparabolicity in mid-infrared quantum cascade lasers. <i>Journal of Applied Physics</i> , 2010 , 108, 113109	2.5	53
154	Electron temperature and mechanisms of hot carrier generation in quantum cascade lasers. <i>Journal of Applied Physics</i> , 2002 , 92, 6921-6923	2.5	51
153	Demonstration of a self-mixing displacement sensor based on terahertz quantum cascade lasers. <i>Applied Physics Letters</i> , 2011 , 99, 081108	3.4	47
152	Optically pumped terahertz laser based on intersubband transitions in a GaN/AlGaIn double quantum well. <i>Journal of Applied Physics</i> , 2005 , 97, 103106	2.5	45
151	Influence of leakage current on temperature performance of GaAs/AlGaAs quantum cascade lasers. <i>Applied Physics Letters</i> , 2002 , 81, 400-402	3.4	42

150	Investigation of thermal effects in quantum-cascade lasers. <i>IEEE Journal of Quantum Electronics</i> , 2006 , 42, 857-865	2	41
149	Designing strain-balanced GaN/AlGaIn quantum well structures: Application to intersubband devices at 1.3 and 1.55 μm wavelengths. <i>Journal of Applied Physics</i> , 2003 , 93, 3194-3197	2.5	41
148	Symmetry of k_{\parallel} Hamiltonian in pyramidal InAs/GaAs quantum dots: Application to the calculation of electronic structure. <i>Physical Review B</i> , 2005 , 72,	3.3	40
147	Effects of rapid thermal annealing on device characteristics of InGaAs/GaAs quantum dot infrared photodetectors. <i>Journal of Applied Physics</i> , 2006 , 99, 114517	2.5	39
146	Intraband absorption in InAs/GaAs quantum dot infrared photodetectors—effective mass versus k_{\parallel} modelling. <i>Semiconductor Science and Technology</i> , 2006 , 21, 1098-1104	1.8	38
145	Influence of doping density on electron dynamics in GaAs/AlGaAs quantum cascade lasers. <i>Journal of Applied Physics</i> , 2006 , 99, 103106	2.5	38
144	Interband and intraband optical transitions in InAs nanocrystal quantum dots: A pseudopotential approach. <i>Physical Review B</i> , 2008 , 78,	3.3	37
143	Population inversion in optically pumped asymmetric quantum well terahertz lasers. <i>Journal of Applied Physics</i> , 1997 , 81, 7135-7140	2.5	36
142	Approximate methods for the solution of quantum wires and dots: Connection rules between pyramidal, cuboidal, and cubic dots. <i>Journal of Applied Physics</i> , 1999 , 86, 5054-5059	2.5	35
141	Density matrix theory of transport and gain in quantum cascade lasers in a magnetic field. <i>Physical Review B</i> , 2007 , 76,	3.3	32
140	Self-consistent energy balance simulations of hole dynamics in SiGeBiTe quantum cascade structures. <i>Journal of Applied Physics</i> , 2004 , 96, 6803-6811	2.5	32
139	Carrier scattering approach to the origins of dark current in mid- and far-infrared (terahertz) quantum-well intersubband photodetectors (QWLPs). <i>IEEE Journal of Quantum Electronics</i> , 2001 , 37, 672-675	2	31
138	Influence of the active region design on output characteristics of GaAs/AlGaAs quantum cascade lasers in a strong magnetic field. <i>Semiconductor Science and Technology</i> , 2006 , 21, 215-220	1.8	30
137	Towards automated design of quantum cascade lasers. <i>Journal of Applied Physics</i> , 2005 , 97, 084506	2.5	30
136	Numerical Rate Equation Modeling of a Ho^{3+} -Co-Doped Tellurite Fiber Laser. <i>Journal of Lightwave Technology</i> , 2009 , 27, 4280-4288	4	29
135	Thermal Modeling of Terahertz Quantum-Cascade Lasers: Comparison of Optical Waveguides. <i>IEEE Journal of Quantum Electronics</i> , 2008 , 44, 680-685	2	29
134	Interwell relaxation times in pBiBiGe asymmetric quantum well structures: Role of interface roughness. <i>Physical Review B</i> , 2007 , 75,	3.3	29
133	Electron-phonon relaxation rates and optical gain in a quantum cascade laser in a magnetic field. <i>Journal of Applied Physics</i> , 2005 , 97, 103109	2.5	29

132	Relationship between carrier dynamics and temperature in terahertz quantum cascade structures: simulation of GaAs/AlGaAs, SiGe/Si and GaN/AlGaN devices. <i>Semiconductor Science and Technology</i> , 2005 , 20, S237-S245	1.8	28
131	Physical model of quantum-well infrared photodetectors. <i>Journal of Applied Physics</i> , 2004 , 96, 269-272	2.5	27
130	Toward Silicon-Based Lasers for Terahertz Sources. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2006 , 12, 1570-1578	3.8	26
129	Comparative study of intersubband absorption in AlGaIn/GaN and AlInN/GaN superlattices: Impact of material inhomogeneities. <i>Physical Review B</i> , 2013 , 88,	3.3	25
128	Electronic structure and optical properties of Sn and SnGe quantum dots. <i>Journal of Applied Physics</i> , 2008 , 103, 103712	2.5	25
127	Intersubband terahertz lasers using four-level asymmetric quantum wells. <i>Journal of Applied Physics</i> , 1999 , 85, 23-28	2.5	25
126	Efficient prediction of terahertz quantum cascade laser dynamics from steady-state simulations. <i>Applied Physics Letters</i> , 2015 , 106, 161105	3.4	24
125	Quantum box energies as a route to the ground state levels of self-assembled InAs pyramidal dots. <i>Journal of Applied Physics</i> , 2000 , 88, 5870-5874	2.5	23
124	Intersubband lifetimes in pBiBiGe terahertz quantum cascade heterostructures. <i>Physical Review B</i> , 2005 , 71,	3.3	22
123	A microscopic model of electron transport in quantum dot infrared photodetectors. <i>Journal of Applied Physics</i> , 2006 , 100, 074502	2.5	22
122	Electron transport in quantum cascade lasers in a magnetic field. <i>Physical Review B</i> , 2006 , 73,	3.3	22
121	Self-consistent scattering model of carrier dynamics in GaAs-AlGaAs terahertz quantum-cascade lasers. <i>IEEE Photonics Technology Letters</i> , 2003 , 15, 15-17	2.2	22
120	Waveguide design for mid- and far-infrared p-Si/SiGe quantum cascade lasers. <i>Semiconductor Science and Technology</i> , 2004 , 19, 76-81	1.8	21
119	Terahertz ambipolar dual-wavelength quantum cascade laser. <i>Optics Express</i> , 2009 , 17, 19926-32	3.3	20
118	Stark shift of the spectral response in quantum dots-in-a-well infrared photodetectors. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 5537-5540	3	20
117	Temperature dependence of terahertz optical transitions from boron and phosphorus dopant impurities in silicon. <i>Applied Physics Letters</i> , 2005 , 87, 101114	3.4	20
116	Photoreflectance and surface photovoltage spectroscopy of beryllium-doped GaAs/AlAs multiple quantum wells. <i>Journal of Applied Physics</i> , 2005 , 98, 023508	2.5	20
115	Coherent vertical electron transport and interface roughness effects in AlGaIn/GaN intersubband devices. <i>Journal of Applied Physics</i> , 2015 , 118, 224308	2.5	19

114	Electronic properties calculation of Ge _{1-x} Si _x Sny ternary alloy and nanostructure. <i>Journal of Non-Crystalline Solids</i> , 2012 , 358, 2096-2098	3.9	19
113	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2010 , 16, 100-105	3.8	19
112	Origin of detection wavelength tuning in quantum dots-in-a-well infrared photodetectors. <i>Applied Physics Letters</i> , 2006 , 88, 251107	3.4	19
111	Aspects of the internal physics of InGaAs/AlAs quantum cascade lasers. <i>Journal of Applied Physics</i> , 2006 , 99, 114505	2.5	19
110	Comparison of the quantum efficiencies of interwell and intrawell radiative transitions in quantum cascade lasers. <i>Applied Physics Letters</i> , 1999 , 75, 1999-2001	3.4	19
109	Electron Transport and Terahertz Gain in Quantum-Dot Cascades. <i>IEEE Photonics Technology Letters</i> , 2008 , 20, 129-131	2.2	18
108	Quantum mechanical scattering investigation of the thermionic and field induced emission components of the dark current in quantum well infrared photodetectors. <i>Journal of Applied Physics</i> , 2002 , 92, 248-252	2.5	18
107	Importance of Polaronic Effects for Charge Transport in CdSe Quantum Dot Solids. <i>Journal of Physical Chemistry Letters</i> , 2014 , 5, 1335-40	6.4	17
106	Selective wavelength tuning of self-assembled InAs quantum dots grown on InP. <i>Applied Physics Letters</i> , 2006 , 88, 193112	3.4	16
105	Dependence of saturation effects on electron confinement and injector doping in GaAs/Al _{0.45} Ga _{0.55} As quantum-cascade lasers. <i>Applied Physics Letters</i> , 2006 , 88, 251109	3.4	16
104	Symmetry-based calculation of single-particle states and intraband absorption in hexagonal GaN/AlN quantum dot superlattices. <i>Journal of Physics Condensed Matter</i> , 2006 , 18, 6249-6262	1.8	16
103	Optically pumped intersublevel Midinfrared lasers based on InAs-GaAs quantum dots. <i>IEEE Journal of Quantum Electronics</i> , 2005 , 41, 1361-1368	2	16
102	Exciton Dynamics in InSb Colloidal Quantum Dots. <i>Journal of Physical Chemistry Letters</i> , 2016 , 7, 31-5	6.4	15
101	Theoretical Modeling of a $\sim \mu\text{m}$ -Doped Tellurite Fiber Laser: The Influence of Cross Relaxation. <i>Journal of Lightwave Technology</i> , 2009 , 27, 4026-4032	4	15
100	Time delay in thin slabs with self-focusing Kerr-type nonlinearity. <i>Physical Review A</i> , 2008 , 77,	2.6	15
99	Model for a pulsed terahertz quantum cascade laser under optical feedback. <i>Optics Express</i> , 2016 , 24, 20554-70	3.3	15
98	Impurity bound-to-unbound terahertz sensors based on beryllium and silicon doped GaAs/AlAs multiple quantum wells. <i>Applied Physics Letters</i> , 2008 , 92, 053503	3.4	14
97	Population-inversion and gain estimates for a semiconductor TASER. <i>IEEE Journal of Quantum Electronics</i> , 2001 , 37, 153-158	2	14

96	A physical model of quantum cascade lasers: Application to GaAs, GaN and SiGe devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 980-986	1.6	13
95	Radiative recombination spectra of p-type δ -doped GaAs/AlAs multiple quantum wells near the Mott transition. <i>Journal of Applied Physics</i> , 2008 , 103, 123108	2.5	12
94	Effect of quantum confinement on shallow acceptor transitions in δ -doped GaAs/AlAs multiple-quantum wells. <i>Applied Physics Letters</i> , 2004 , 84, 735-737	3.4	12
93	The effect of inter-dot separation on the finite difference solution of vertically aligned coupled quantum dots. <i>Computer Physics Communications</i> , 2003 , 155, 236-243	4.2	12
92	Magnetic-field tunable terahertz quantum well infrared photodetector. <i>Journal of Applied Physics</i> , 2005 , 98, 084509	2.5	12
91	Phase-breaking effects in double-barrier resonant tunneling diodes with spin-orbit interaction. <i>Journal of Applied Physics</i> , 2010 , 108, 044506	2.5	11
90	Coherent transport description of the dual-wavelength ambipolar terahertz quantum cascade laser. <i>Journal of Applied Physics</i> , 2011 , 109, 013111	2.5	10
89	Optimal design of GaN-AlGaN Bragg-confined structures for intersubband absorption in the near-infrared spectral range. <i>IEEE Journal of Quantum Electronics</i> , 2003 , 39, 1297-1304	2	10
88	Monotonic Evolution of the Optical Properties in the Transition from Three- to Quasi-Two-Dimensional Quantum Confinement in InAs Nanorods. <i>Journal of Physical Chemistry C</i> , 2010 , 114, 6901-6908	3.8	9
87	Room temperature operation of AlGaIn/GaN quantum well infrared photodetectors at a $3\mu\text{m}$ wavelength range. <i>Semiconductor Science and Technology</i> , 2007 , 22, 1240-1244	1.8	9
86	Effect of quantum-well confinement on acceptor state lifetime in δ -doped GaAs/AlAs multiple quantum wells. <i>Applied Physics Letters</i> , 2003 , 83, 3719-3721	3.4	9
85	Solid-state terahertz sources using quantum-well intersubband transitions. <i>IEEE Transactions on Microwave Theory and Techniques</i> , 2000 , 48, 645-652	4.1	9
84	Electron transport in n-doped Si/SiGe quantum cascade structures. <i>Journal of Applied Physics</i> , 2007 , 101, 093703	2.5	8
83	Dilute magnetic semiconductor quantum-well structures for magnetic field tunable far-infrared/terahertz absorption. <i>IEEE Journal of Quantum Electronics</i> , 2004 , 40, 1614-1621	2	8
82	Nonequilibrium electron heating in inter-subband terahertz lasers. <i>Journal of Applied Physics</i> , 2002 , 91, 904-910	2.5	8
81	Origin of terminal voltage variations due to self-mixing in terahertz frequency quantum cascade lasers. <i>Optics Express</i> , 2016 , 24, 21948-56	3.3	8
80	The role of temperature in quantum-cascade laser waveguides. <i>Journal of Computational Electronics</i> , 2012 , 11, 137-143	1.8	7
79	Active glass waveguide amplifier on GaAs by UV-pulsed laser deposition and femtosecond laser inscription. <i>Laser Physics Letters</i> , 2012 , 9, 329-339	1.5	7

78	Laterally pumped GaAs/AlGaAs quantum wells as sources of broadband terahertz radiation. <i>Journal of Applied Physics</i> , 2007 , 102, 073715	2.5	7
77	Quantum mechanical scattering investigation of the dark current in quantum well infrared photodetectors (QWIPs). <i>Infrared Physics and Technology</i> , 2003 , 44, 473-480	2.7	7
76	Surface plasmon waveguides with gradually doped or NiAl intermetallic compound buried contact for terahertz quantum cascade lasers. <i>Journal of Applied Physics</i> , 2003 , 94, 3249-3252	2.5	7
75	A microscopic model of quantum well infrared photodetectors (QWIP). <i>Infrared Physics and Technology</i> , 2005 , 47, 3-8	2.7	7
74	Quantum Dots as Sources and Detectors of Mid- and Far-Infrared Radiation: Theoretical Models. <i>Acta Physica Polonica A</i> , 2009 , 116, 464-467	0.6	7
73	Impurity-related photoluminescence line shape asymmetry in GaAs/AlAs multiple quantum wells: Fractional-dimensional space approach. <i>Journal of Applied Physics</i> , 2010 , 107, 093109	2.5	6
72	Saturation of intersubband transitions in p-doped GaAs/AlGaAs quantum wells. <i>Applied Physics Letters</i> , 2008 , 92, 183104	3.4	6
71	Stark ladders as tunable far-infrared emitters. <i>Journal of Applied Physics</i> , 1998 , 84, 5175-5179	2.5	6
70	Numerical solution to the general one-dimensional diffusion equation in semiconductor heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 1996 , 197, 81-90	1.3	6
69	Electronic states and intraband terahertz optical transitions in InGaAs quantum rods. <i>Journal of Applied Physics</i> , 2012 , 111, 073110	2.5	5
68	Electronic structure and optical transitions in Sn and SnGe quantum dots in a Si matrix. <i>Microelectronics Journal</i> , 2009 , 40, 483-485	1.8	5
67	MBE growth and transport properties of silicon doped GaAs/AlAs quantum well structures for terahertz frequency detection. <i>Journal of Crystal Growth</i> , 2010 , 312, 1761-1765	1.6	5
66	Effects of interface imperfections on the Zeeman splitting of excitons in diluted magnetic semiconductor quantum wells. <i>The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties</i> , 1997 , 75, 349-361		5
65	Wide wavelength tuning of GaAs _{1-x} Ga _x As bound-to-continuum quantum cascade lasers by aluminum content control. <i>Applied Physics Letters</i> , 2008 , 92, 141111	3.4	5
64	Effect of GaP strain compensation layers on rapid thermally annealed InGaAs/GaAs quantum dot infrared photodetectors grown by metal-organic chemical-vapor deposition. <i>Applied Physics Letters</i> , 2007 , 91, 073515	3.4	5
63	Mechanisms of carrier transport and temperature performance evaluation in terahertz quantum cascade lasers. <i>Semiconductor Science and Technology</i> , 2004 , 19, S104-S106	1.8	5
62	Occupancy calculations for quantum-dot-based memory devices. <i>New Journal of Physics</i> , 2004 , 6, 30-30	2.9	5
61	Influence of injector doping density and electron confinement on the properties of GaAs/Al _{0.45} Ga _{0.55} As quantum cascade lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 411-414		4

60	n-Si/SiGe quantum cascade structures for THz emission. <i>Journal of Luminescence</i> , 2006 , 121, 311-314	3.8	4
59	Optical cavities for Si/SiGe terahertz quantum cascade emitters. <i>Optical Materials</i> , 2005 , 27, 851-854	3.3	4
58	SUSY transformation of guided modes in semiconductor waveguides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 3552-3555		4
57	Design and simulation of InGaAs/AlAsSb quantum-cascade lasers for short wavelength emission. <i>Applied Physics Letters</i> , 2005 , 87, 141109	3.4	4
56	Optical and Terahertz Characterization of Be-Doped GaAs/AlAs Multiple Quantum Wells. <i>Acta Physica Polonica A</i> , 2005 , 107, 328-332	0.6	4
55	Interdiffusion effects and line broadening of hole intersubband absorption in complex GaAs/AlGaAs quantum well structures. <i>Journal of Applied Physics</i> , 2010 , 107, 113107	2.5	3
54	Comparison of SiO ₂ , Si ₃ N ₄ , As ₂ S ₃ , and Ge _{0.25} Se _{0.75} dielectric layers for InP- and GaAs-based material systems for midinfrared quantum cascade laser waveguides. <i>Journal of Applied Physics</i> , 2009 , 106, 053104	2.5	3
53	Nonparabolicity effects and the spin-split electron dwell time in symmetric III-V double-barrier structures. <i>Microelectronics Journal</i> , 2009 , 40, 611-614	1.8	3
52	Differential surface photovoltage spectroscopy of δ -doped GaAs/AlAs multiple quantum wells below and close to Mott transition. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 82-88	1.3	3
51	Electric field domains in p-Si/SiGe quantum cascade structures. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 189-195	2.9	3
50	Modelling and simulation of electronic and optical responses of quantum well infrared photodetectors (QWIPs). <i>Journal Physics D: Applied Physics</i> , 2006 , 39, 1773-1780	3	3
49	Effect of confinement on the lifetimes of shallow impurity states in quantum wells. <i>Applied Physics Letters</i> , 2004 , 85, 5257-5259	3.4	3
48	Binding energy and dynamics of Be acceptor levels in AlAs/GaAs multiple quantum wells. <i>Journal of Luminescence</i> , 2004 , 108, 181-184	3.8	3
47	Simulation of Carrier Transport in p-Si/SiGe Quantum Cascade Emitters. <i>Journal of Computational Electronics</i> , 2003 , 2, 353-356	1.8	3
46	Terahertz Detection with δ -Doped GaAs/AlAs Multiple Quantum Wells. <i>Acta Physica Polonica A</i> , 2008 , 113, 909-912	0.6	3
45	Stable perfectly-matched-layer boundary conditions for finite-difference time-domain simulation of acoustic waves in piezoelectric crystals. <i>Journal of Computational Physics</i> , 2013 , 253, 239-246	4.1	2
44	Effect of ion implantation on quantum well infrared photodetectors. <i>Infrared Physics and Technology</i> , 2007 , 50, 106-112	2.7	2
43	Photo- and electro-reflectance spectroscopy of δ -doped GaAs/AlAs multiple quantum well structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 412-421	1.6	2

42	Far-infrared absorption studies of Be acceptors in Edoped GaAs/AlAs multiple quantum wells 2006 , 49, 702-708		2
41	Study of Be Edoped GaAs/AlAs multiple quantum wells by the surface photovoltage spectroscopy. <i>Applied Surface Science</i> , 2006 , 252, 5437-5440	6.7	2
40	Towards a Si/SiGe Quantum Cascade Laser for Terahertz Applications. <i>Materials Research Society Symposia Proceedings</i> , 2004 , 832, 12		2
39	Monte Carlo Simulations of Hole Dynamics in Si/SiGe Quantum Cascade Structures. <i>Journal of Computational Electronics</i> , 2002 , 1, 191-194	1.8	2
38	The effect of the localization in a quantum well on the lifetime of the states of shallow impurity centers. <i>Semiconductors</i> , 2005 , 39, 58	0.7	2
37	Quantum cascade lasers in magnetic field: An active region model. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 1812-1816	1.3	2
36	GaAs/Al _{0.45} Ga _{0.55} As Double Phonon Resonance Quantum Cascade Laser. <i>AIP Conference Proceedings</i> , 2005 ,	0	2
35	Anticrossing effects in the design of MIR intersubband semiconductor lasers. <i>Journal of Modern Optics</i> , 2000 , 47, 1791-1801	1.1	2
34	Normal Incidence Mid-Infrared Photocurrent in AlGa _N /Ga _N Quantum Well Infrared Photodetectors. <i>Acta Physica Polonica A</i> , 2005 , 107, 174-178	0.6	2
33	Intervalley Scattering and the Role of Indirect Band Gap AlAs Barriers: Application to GaAs/AlGaAs Quantum Cascade Lasers. <i>Acta Physica Polonica A</i> , 2008 , 113, 891-902	0.6	2
32	Mid-infrared entangled photon generation in optimised asymmetric semiconductor quantum wells. <i>Superlattices and Microstructures</i> , 2016 , 90, 107-116	2.8	1
31	Strong heavy-to-light hole intersubband absorption in the valence band of carbon-doped GaAs/AlAs superlattices. <i>Journal of Applied Physics</i> , 2013 , 113, 053103	2.5	1
30	Self-mixing effect in THz quantum cascade lasers: Applications in sensing and imaging 2013 ,		1
29	Magnetotunneling in resonant tunneling structures with spin Orbit interaction. <i>Journal of Applied Physics</i> , 2011 , 110, 064507	2.5	1
28	The effect of small elongations on the electronic and optical signatures in InAs nanocrystal quantum dots. <i>Journal of Physics Condensed Matter</i> , 2009 , 21, 144212	1.8	1
27	Intervalley scattering in GaAs/AlGaAs quantum wells and quantum cascade lasers. <i>Microelectronics Journal</i> , 2009 , 40, 577-580	1.8	1
26	Dependence of Threshold Current Density on the Waveguide Ridge Width in Quantum-Cascade Lasers. <i>IEEE Journal of Quantum Electronics</i> , 2010 , 46, 1320-1326	2	1
25	Optical losses in dielectric apertured terahertz VCSEL. <i>Optics and Laser Technology</i> , 2004 , 36, 575-580	4.2	1

24	Hole transport simulations in SiGe cascade quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 907-910	3	1
23	In search of a Si/SiGe THz quantum cascade laser		1
22	Geometrical effects on the charge/discharge properties of quantum dot flash memories. <i>Superlattices and Microstructures</i> , 2003 , 34, 241-244	2.8	1
21	Modeling the capture probability and enhancing the photoconductive gain in quantum well infrared photodetectors (QWIPs). <i>Infrared Physics and Technology</i> , 2003 , 44, 481-485	2.7	1
20	Electron-Nuclear spin transfer in quantum-dot networks. <i>Nanotechnology</i> , 2005 , 16, S266-S272	3.4	1
19	A Single-Band Constant-Confining-Potential Model for Self-Assembled InAs/GaAs Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 642, 141		1
18	Quantum well intersubband transitions as a source of terahertz radiation		1
17	Experimental Study of Optical Transitions in Be-Doped GaAs/AlAs Multiple Quantum Wells. <i>Acta Physica Polonica A</i> , 2005 , 107, 245-249	0.6	1
16	Radiative Recombination Spectra of Heavily p-Type-Doped GaAs/AlAs MQWs. <i>Acta Physica Polonica A</i> , 2008 , 113, 963-966	0.6	1
15	Anticrossing effects in the design of MIR intersubband semiconductor lasers		1
14	Charge Carrier Transport in Quantum Cascade Lasers in Strong Magnetic Field. <i>Acta Physica Polonica A</i> , 2011 , 119, 99-102	0.6	1
13	Optical feedback effects on terahertz quantum cascade lasers: modelling and applications 2016 ,		1
12	Heavy-to-light hole intersubband absorption in the valence band of GaAs/AlAs heterostructures. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1509, 1		
11	Comparative Analysis of 8µm GaAs/AlGaAs Quantum Cascade Lasers with Different Injector Doping. <i>Materials Science Forum</i> , 2006 , 518, 29-34	0.4	
10	Symmetry based calculation of electronic structure and intraband absorption in GaN/AlN hexagonal quantum dot superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 3939-3942		
9	Theoretical modelling of electron transport in InAs/GaAs quantum dot superlattices. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 3770-3773		
8	Lasing in spin-polarized terahertz quantum cascade structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4401-4404		
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